

This diode network is designed to provide an integrated solution for the active termination of a single high-speed data signal to eliminate signal undershoot and overshoot. The network has the added benefit of acting to suppress any ESD voltage events by shunting the energy to ground assuring maximum reliability of electronic systems in the field. Trigger levels are defined by the positive and negative bias levels set by the user.

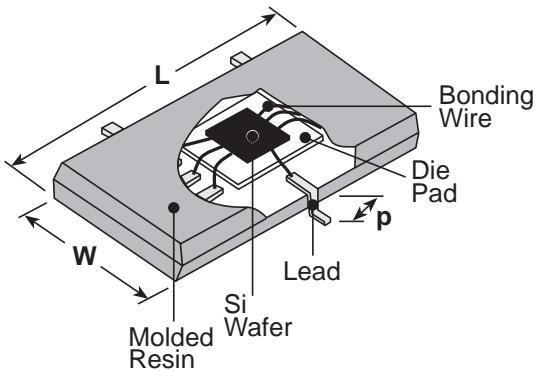
features

- Negligible reverse recovery time
- Low capacitance
- Low forward voltage drop
- 18-channel terminator in a single package
- Resolved bus impedance mismatch

applications

- Termination of data/control signals @ ≥ 66 MHz
- Dynamic RAM bus termination
- RISC architecture

dimensions and construction



Size Code	Dimensions inches (mm)		
	L	W	p
S03	.115 (2.92)	.051 (1.30)	.020 (0.51)

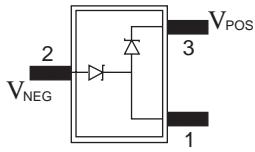
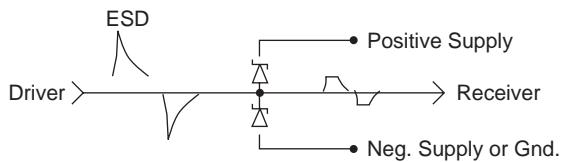
ordering information

New Part #	DN8	S03	L	TE
Type		Package Symbol	Termination Material	Packaging
		Package type symbol + number of pins SOT23: S03	L: SnPb	TE: 7" embossed plastic tape

For further information on packaging, please refer to Appendix C.

Specifications given herein may be changed at any time without prior notice. Please confirm technical specifications before you order and/or use.

11/01/03

circuit schematic

application schematic

applications and ratings

Part Designation	Forward Voltage	Reverse Breakdown Voltage	Leakage Current	Capacitance	Channel Clamp Voltage	ESD Voltage Capability	Operating Temperature Range	Supply Voltage (Vp ~ Vn)	Continuous Forward Current*	Total Power
DN8	0.6 to 0.95V	9.5 to 11V	1uA	2pF	±10V	16kV	-40°C to +85°C	8V	50mA	1W

* One diode conducting

environmental applications
Performance Characteristics

Parameter	Maximum ΔR	Test Method
Resistance to Soldering Heat	+0.25%	MIL-R-55342 4.7.7
Short Time Overload	+0.50%	MIL-R-55342 4.7.5
Moisture Resistance	+0.50%	MIL-STD-202 method 103
Thermal Shock	+0.50%	MIL-STD-202 method 107
H.A.S.T.	+1%	2 Atm., 121°C, 96 hrs